JJMICROELECTRONICS

40V, 209A, 1.2mΩ N-channel Power SGT MOSFET

JMSH04014G4L

Features

- Excellent $R_{DS(ON)}$ and Low Gate Charge
- 100% UIS Tested
- 100% ΔVds Tested
- Halogen-free; RoHS-compliant

Applications

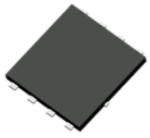
- Load Switch
- PWM Application
- Power Management

Product Summary

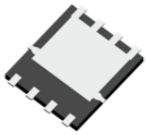
Parameters	Value	Unit
V_{DSS}	40	V
$V_{GS(th)_Typ}$	2.8	V
I_D(@V_{GS}=10V)	209	A
$R_{DS(ON)_Typ}$(@V_{GS}=10V)	1.2	mΩ

RoHS

Top View

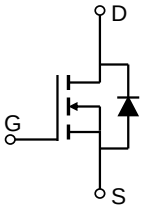


Bottom View



PDFN5X6-8L

Pin Assignment



Schematic Diagram

Ordering Information

Device	Marking	MSL	Form	Package	Reel(pcs)	Per Carton (pcs)
JMSH04014G4L-13	SH040144L	1	Tape&Reel	PDFN5x6-8L	5000	50000

Absolute Maximum Ratings (@ T_C = 25°C unless otherwise specified)

Symbol	Parameter		Value	Unit
V_{DS}	Drain-to-Source Voltage		40	V
V_{GS}	Gate-to-Source Voltage		±20	V
I_D	Continuous Drain Current	T_C = 25°C	209	A
		T_C = 100°C	148	
I_{DM}	Pulsed Drain Current (1)		Refer to Fig.4	A
E_{AS}	Single Pulsed Avalanche Energy (2)		389	mJ
P_D	Power Dissipation	T_C = 25°C	107	W
		T_C = 100°C	54	
T_J, T_{STG}	Junction & Storage Temperature Range		-55 to 175	°C

Thermal Characteristics

Symbol	Parameter	Max	Unit
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient(3)	46	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.4	

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Electrical Characteristics (T_J = 25°C unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	I_D = 250μA, V_{GS} = 0V	40	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 32V, V_{GS} = 0V	-	-	1.0	μA
I_{GSS}	Gate-Body Leakage Current	V_{DS} = 0V, V_{GS} = ±20V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250μA	2.0	2.8	4.0	V
$R_{DS(ON)}$	Static Drain-Source ON-Resistance(4)	V_{GS} = 10V, I_D = 20A	-	1.2	1.4	mΩ
Dynamic Characteristics						
R_g	Gate Resistance	f = 1MHz	-	1.9	-	Ω
C_{iss}	Input Capacitance	V_{GS} = 0V, V_{DS} = 20V, f = 1MHz	-	3859	5250	pF
C_{oss}	Output Capacitance		-	1129	1550	pF
C_{rss}	Reverse Transfer Capacitance		-	70	150	pF
Q_g	Total Gate Charge	V_{GS} = 0 to 10V V_{DS} = 20V, I_D = 20A	-	59	-	nC
Q_{gs}	Gate Source Charge		-	16	-	nC
Q_{gd}	Gate Drain("Miller") Charge		-	12	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-On DelayTime	V_{GS} = 10V, V_{DD} = 20V I_D= 20A, R_{GEN} = 3Ω	-	25	-	ns
t_r	Turn-On Rise Time		-	26	-	ns
$t_{d(off)}$	Turn-Off DelayTime		-	38	-	ns
t_f	Turn-Off Fall Time		-	12	-	ns
Body Diode Characteristics						
I_S	Maximum Continuous Body Diode Forward Current		-	-	209	A
I_{SM}	Maximum Pulsed Body Diode Forward Current		-	-	836	A
V_{SD}	Body Diode Forward Voltage	V_{GS} = 0V, I_S = 20A	-		1.2	V
trr	Body Diode Reverse Recovery Time	I_F = 20A, di/dt = 100A/us	21	41	62	ns
Qrr	Body Diode Reverse Recovery Charge		-	41	-	nC

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
2. E_{AS} condition: Starting T_J=25C, V_{DD}=20V, V_{GS}=10V, R_G=25ohm, L=3mH, I_{AS}=16.1A, V_{DD}=0V during time in avalanche.
3. $R_{\theta JA}$ is measured with the device mounted on a 1inch^2 pad of 2oz copper FR4 PCB.
4. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%.

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Typical Performance Characteristics

Figure 1: Power De-rating

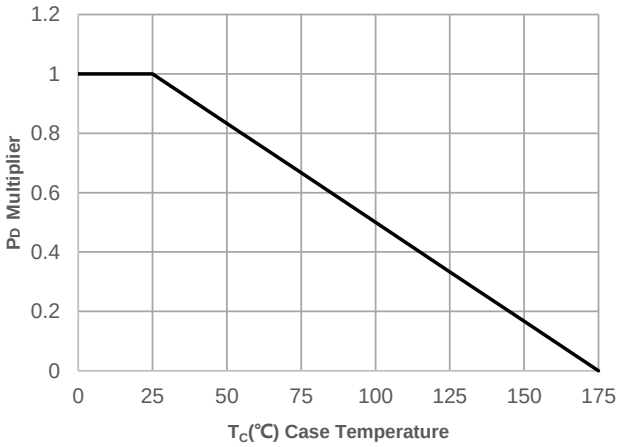


Figure 2: Current De-rating

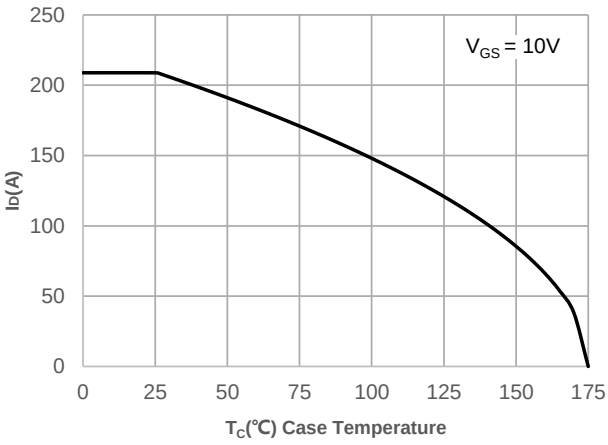


Figure 3: Normalized Maximum Transient Thermal Impedance

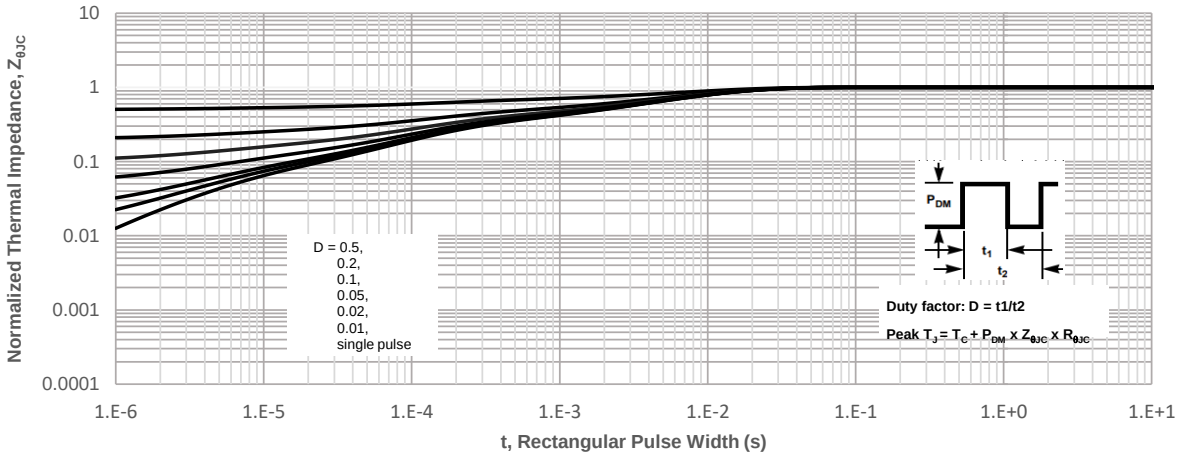
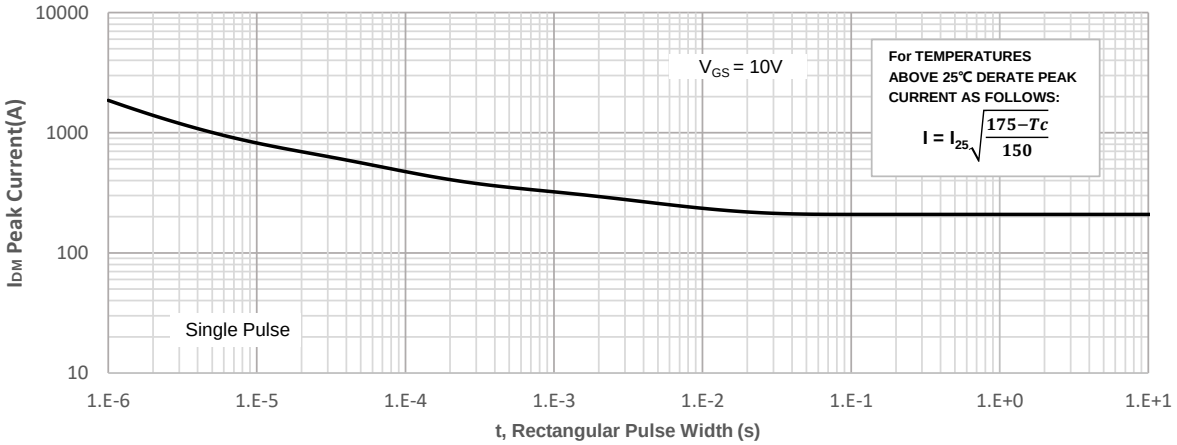


Figure 4: Peak Current Capacity



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Typical Performance Characteristics

Figure 5: Output Characteristics

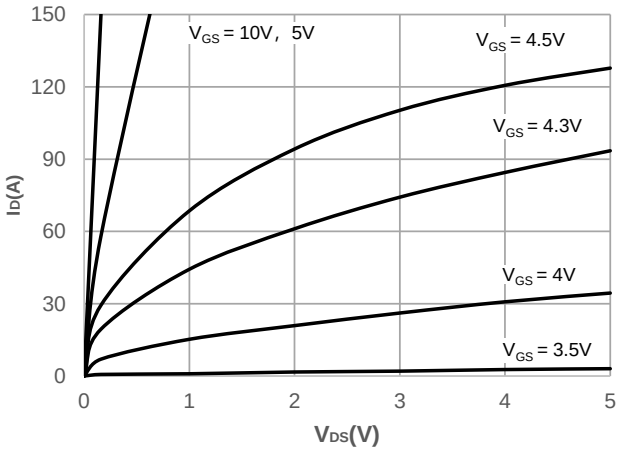


Figure 6: Typical Transfer Characteristics

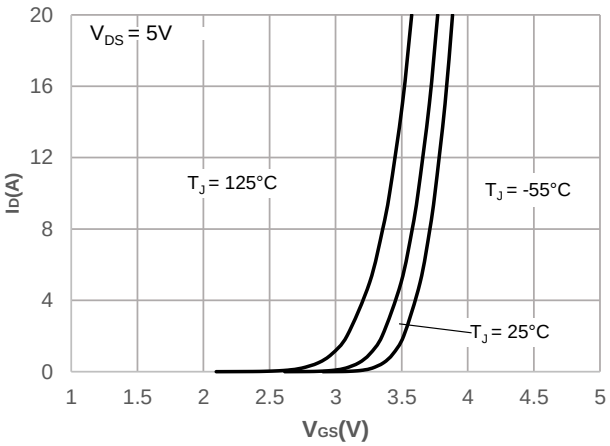


Figure 7: On-resistance vs. Drain Current

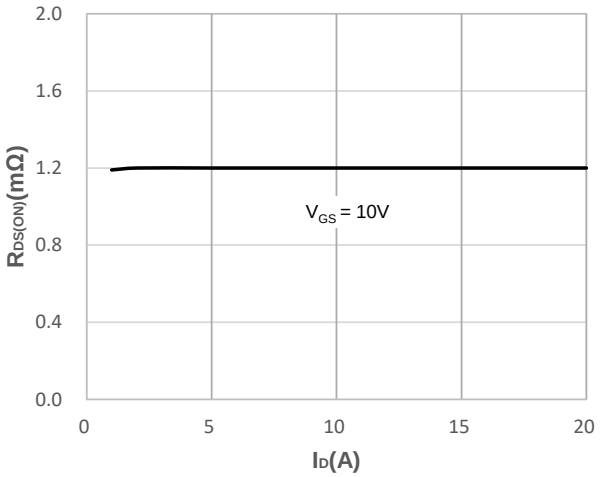


Figure 8: Body Diode Characteristics

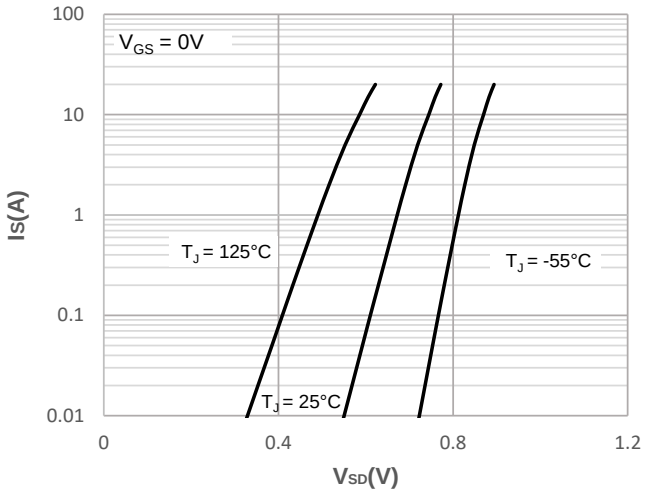


Figure 9: Gate Charge Characteristics

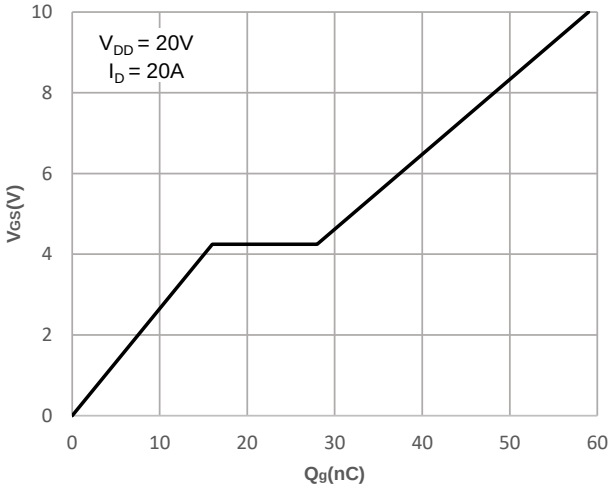
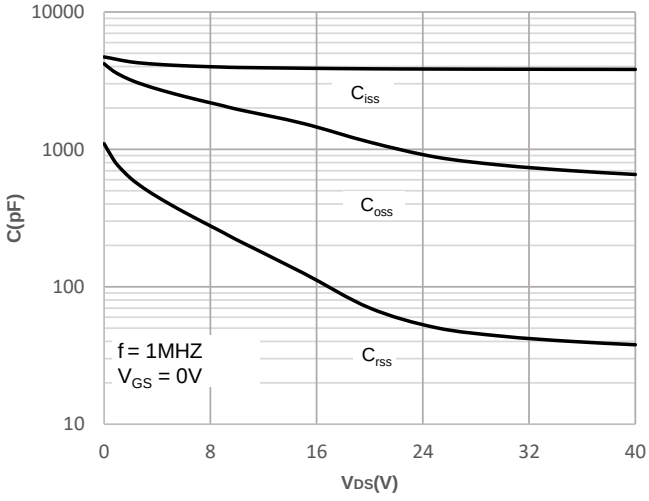


Figure 10: Capacitance Characteristics



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Typical Performance Characteristics

Figure 11: Normalized Breakdown Voltage vs. Junction Temperature

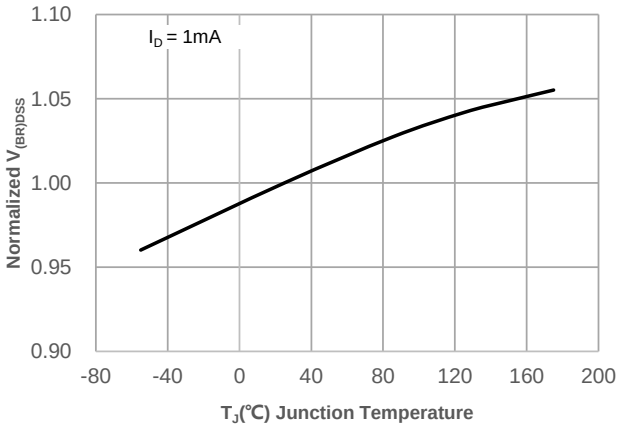


Figure 12: Normalized on Resistance vs. Junction Temperature

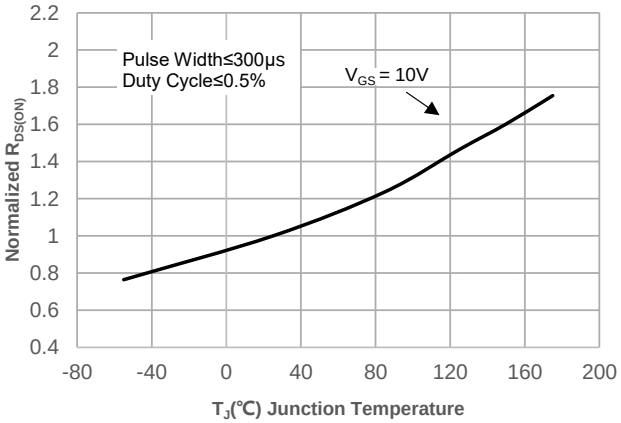


Figure 13: Normalized Threshold Voltage vs. Junction Temperature

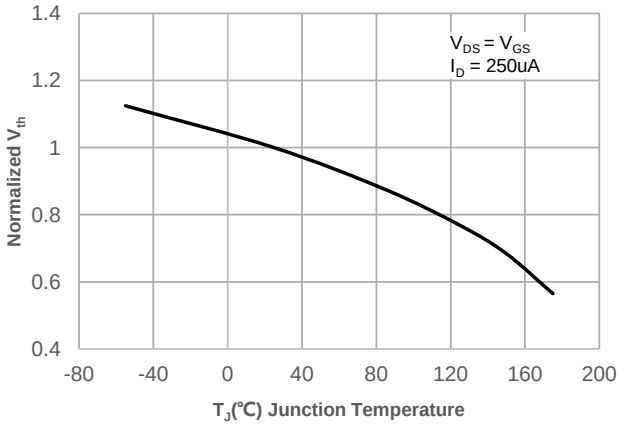


Figure 14: $R_{DS(ON)}$ vs. V_{GS}

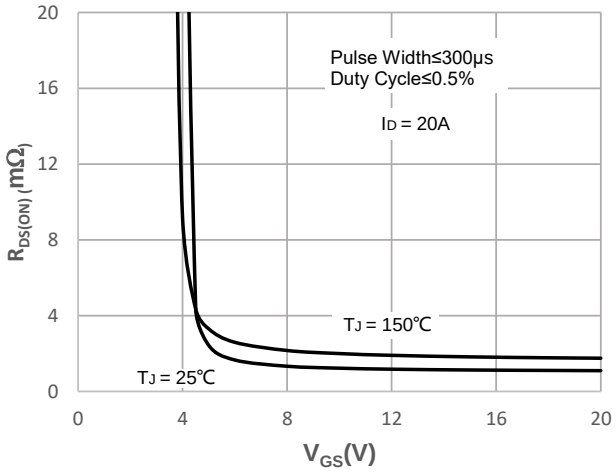
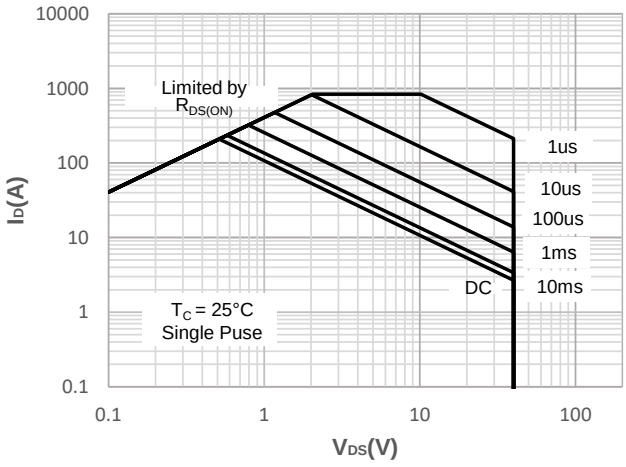


Figure 15: Maximum Safe Operating Area



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Test Circuit

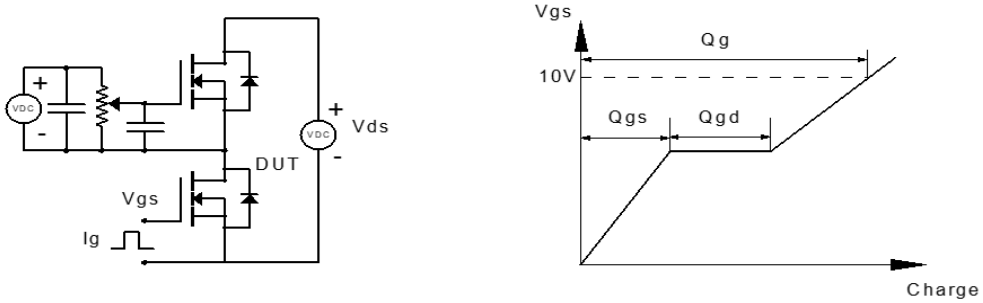

Figure 1: Gate Charge Test Circuit & Waveform

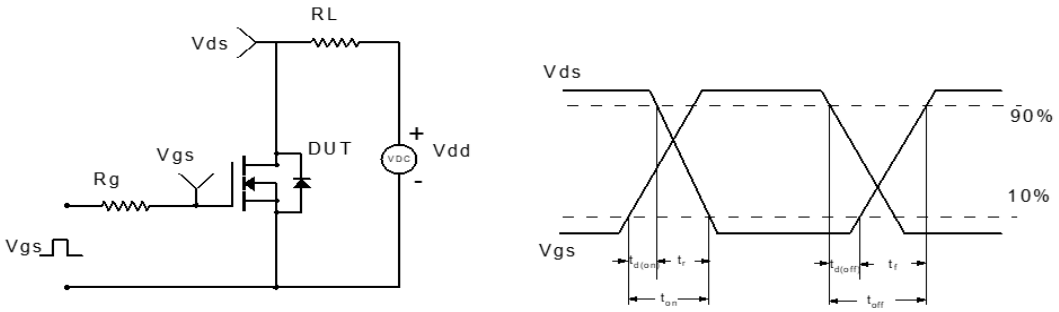

Figure 2: Resistive Switching Test Circuit & Waveform

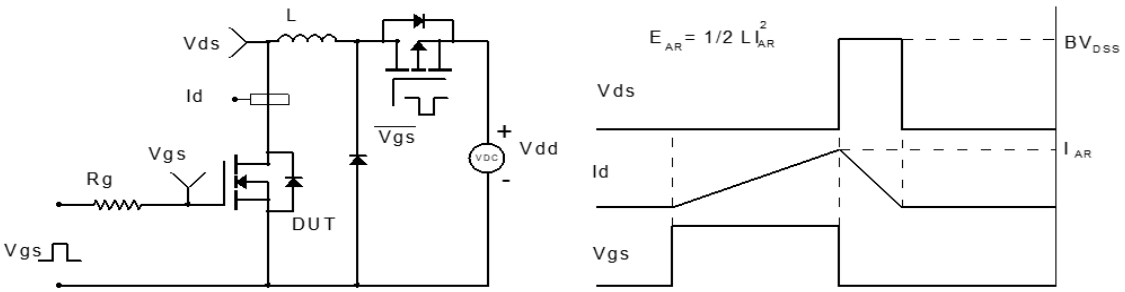

Figure 3: Unclamped Inductive Switching Test Circuit& Waveform

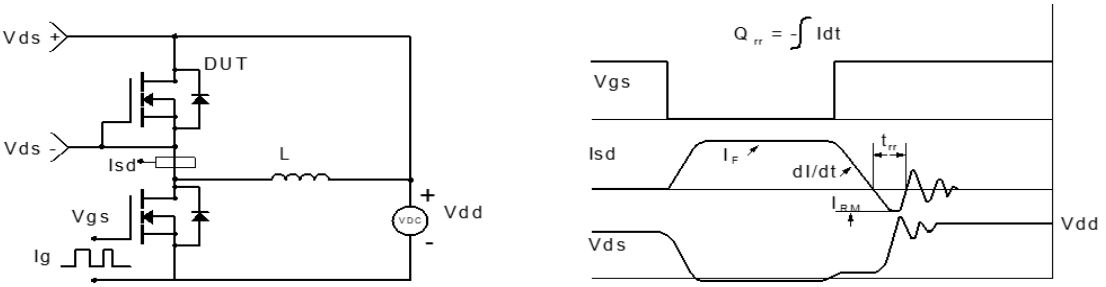

Figure 4: Diode Recovery Test Circuit & Waveform

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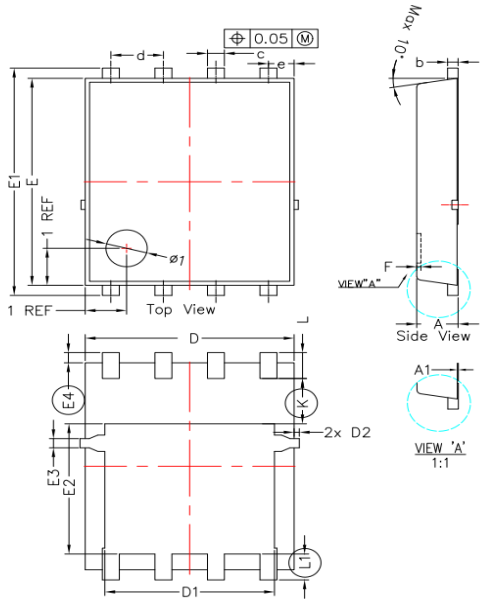
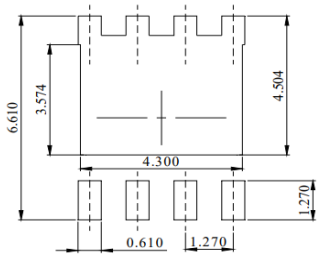
Package Mechanical Data(PDFN5X6-8L)



SYMBOLS	DIMENSION IN MM			DIMENSION IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
*A	0.900	1.000	1.150	0.035	0.039	0.045
A1	0.000	---	0.050	0.000	----	0.002
b	0.246	0.254	0.350	0.010	0.010	0.014
*C	0.310	0.410	0.510	0.012	0.016	0.020
d		1.27BSC			0.050BSC	
*D	4.950	5.050	5.150	0.195	0.199	0.203
D1	4.000	4.100	4.200	0.157	0.161	0.165
*D2		0.125REF			0.005REF	
e		0.62BSC			0.024BSC	
*E	5.500	5.600	5.700	0.217	0.220	0.224
*E1	6.050	6.150	6.250	0.238	0.242	0.246
E2	3.425	3.525	3.625	0.135	0.139	0.143
E3		0.250REF			0.010REF	
* E4		0.275REF			0.011REF	
F	-	-	0.100	-	-	0.004
*L	0.500	0.600	0.700	0.02	0.02	0.03
L1	0.600	0.700	0.800	0.02	0.03	0.03
K		1.225REF			0.05REF	

Recommended Soldering Footprint



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